COURSE CODE	COURSE NAME	L-T-P-C	INT	YEAR (TRODU	
EC467	PATTERN RECOGNITION	3-0-0-3		2016	
Prerequis		3-0-0-3		2010	
Course ob					
	introduce the fundamental algorithms for pattern reco	onition			
	instigate the various classification and clustering techniqu	-			
	Review of Probability Theory and Probability distr		ntrodu	uction to	Pattern
•	n and its applications, Bayesian decision theory,				
	n, ML estimation, EM algorithm, Supervised and				
	Linear Discriminant Functions, Non-parametric meth				
sequential	data classification, Linear models for regression and c	lassificatio	on, Clu	stering	
Expected					
The studer	ts will be able to				
i.	Design and construct a pattern recognition system				
ii.	Know the major approaches in statistical and syntacti				
iii.	Become aware of the theoretical issues involved in p	battern reco	ognitic	on systen	n design
	such as the curse of dimensionality.				
iv. Text Book	Implement pattern recognition techniques				
	, ,		ne ana	lysis, Joł	n
1. Mc	rton Nadier and Eric Smith P., Pattern Recognition Er w York, 1993.	ngineering,	John	Wiley &	Sons,
2. Ro	bert J. Schalkoff, Pattern Recognition : Statistical, Stru	uctural and	Neura	al Approa	aches,
	n Wiley & Sons Inc., New York, 2007.				
	heodoridis and K. Koutroumbas, Pattern Recognition	, 4/e, Acad	emic l	Press, 20	09.
	m Mitchell, Machine Learning, McGraw-Hill	D 11	· a		
	a and Gonzales, Pattern Recognition Principles, Wesle	ey Publicat	ion Co	ompany,	
LO	ndon, 1974. Course Plan				
	Course rian				
Module	Course content				End
					Sem
				Hours	Exam
					Marks
	Introduction: Basics of pattern recognition sy	ystem, va	rious	6	
	applications, Machine Perception, classification	, ,	attern	3	
Ι	recognition systems	-			15%
	Design of Pattern recognition system, Pattern recogni	tion Life C	lycle	2	

			r
	 Statistical Pattern Recognition: Review of probability theory, Gaussian distribution, Bayes decision theory and Classifiers, Optimal solutions for minimum error and minimum risk criteria, Normal density and discriminant functions, Decision surfaces Parameter estimation methods: Maximum-Likelihood estimation, Expectation-maximization method, Bayesian parameter estimation 	4	
		2	
Π	Concept of feature extraction and dimensionality, Curse of dimensionality, Dimension reduction methods - Fisher discriminant analysis, Principal component analysis Hidden Markov Models (HMM) basic concepts, Gaussian mixture models.	6	15%
	FIRST INTERNAL EXAM		
	Non-Parameter methods: Non-parametric techniques for density estimation - Parzen-window method, K-Nearest Neighbour method.	3	
III	Non-metric methods for pattern classification: Non-numeric data or nominal data Decision trees: Concept of construction, splitting of nodes, choosing of attributes, overfitting, pruning	3	15%
IV	Linear Discriminant based algorithm: Perceptron, Support Vector Machines	5	15%
	SECOND INTERNAL EXAM		·
V	Multilayer perceptrons, Back Propagation algorithm, Artificial Neural networks	4	20%
	Classifier Ensembles: Bagging, Boosting / AdaBoost	3	
VI	Unsupervised learning: Clustering - Criterion functions for clustering, Algorithms for clustering: K-means and Hierarchical methods, Cluster validation	5	20%
	END SEMESTER EXAM		

The question paper shall consist of three parts. Part A covers modules I and II, Part B covers modules III and IV, and Part C covers modules V and VI. Each part has three questions uniformly covering the two modules and each question can have maximum four subdivisions. In each part, any two questions are to be answered. Mark patterns are as per the syllabus with 70% for theory and 30% for logical/numerical problems, derivation and proof.

LSIU.

COURSE			YEAR	OF	
CODE	COURSE NAMEL-T-P-C	IN	TRODU	CTION	
EC461	MICROWAVE DEVICES AND CIRCUITS 3-0-0-3		201	6	
Prerequisite: H	Prerequisite: EC403 Microwave & Radar Engineering				
Course objecti	ves:				
	y microwave semiconductor devices & applications.				
	y microwave sources and amplifiers.	N . A			
	yse microwave networks.	M			
	duce microwave integrated circuits.				
Syllabus:					
generation and Microwave an Microwave fil implementation Diode control of Expected outc	ome:	ar trans s, Sign lter tra ts of ir	sistors, M nal flow insforma ntegrated	MESFET, graphs, tion and circuits,	
	ill be able to understand with active & passive microwave		s & com	ponents	
	ave communication systems and analyse microwave netwo	orks.	_		
Text Books:					
2. Robert	 Pozar, Microwave Engineering, 4/e, Wiley India, 2012 Collin, Foundation of Microwave Engineering, 2/e, Wil Y. Liao, Microwave Devices and Circuits, 3/e, Pearson Education 	•			
References:					
Internat 2. I Knepp	i Bhat and Shiban K. Koul: Stripline-like Transmission I ional (P) Ltd, 1989. o, J. Fabian, et al., Microwaye Integrated Circuits, BSP, In loratsky, Passive RF and Microwaye Integrated Circuits, F	ndia, 20	06.	New Age	
	Course Plan				
Module	Course contents	/	Hours	End Sem. Exam	
	duction, Characteristic, features of microwaves, Limitati	on of		Marks	
	entional solid state devices at Microwave.		1		
Gunt I theor	n – effect diodes – Gunn effect, Ridley – Watkins-H y, Modes of operation, Limited space – Charge accumu a) mode of Gunn diode.	ilsum	1		
I Guni (LSA Micr	n – effect diodes – Gunn effect, Ridley – Watkins-H y, Modes of operation, Limited space – Charge accumu	ilsum lation ration,		Marks	
I Guni (LSA Micr Powe Bipo	n – effect diodes – Gunn effect, Ridley – Watkins-H y, Modes of operation, Limited space – Charge accumu a) mode of Gunn diode. owave generation and amplification. Structure, Oper	ilsum lation ation, s	2	Marks	
I Gun theor (LSA Micr Powe Bipo Oper II Micr stabi	n – effect diodes – Gunn effect, Ridley – Watkins-H y, Modes of operation, Limited space – Charge accumu a) mode of Gunn diode. owave generation and amplification. Structure, Oper er output and efficiency of IMPATT and TRAPATT diode lar transistors – biasing, FET – biasing, MESFET – Stru ation. owave amplifiers and oscillators – Amplifiers – Gain lity, Single stage transistor amplifier design.	ilsum lation ation, s cture,	2	Marks	
I Gun theor (LSA Micr Powe Bipo Oper II Micr stabi	n – effect diodes – Gunn effect, Ridley – Watkins-H y, Modes of operation, Limited space – Charge accumu a) mode of Gunn diode. owave generation and amplification. Structure, Oper er output and efficiency of IMPATT and TRAPATT diode lar transistors – biasing, FET – biasing, MESFET – Stru ation. owave amplifiers and oscillators – Amplifiers – Gain	ilsum lation ation, s cture,	2 2 4	Marks	

IIISignal flow graphs. Impedance matching and tuning – Matching with lumped elements, Single stub tuning, Double stub tuning. Quarter wave transformer, Theory of small reflections.IS%IVMicrowave filters – Periodic structures – Analysis of infinite periodic structures and terminated periodic structures, Filter design by image parameter method – Constant k, m-derived and composite. Filter design by insertion loss method. Filter transformation and implementation.715%IVIntroduction to MICSs:-Technology of hybrid MICs, monolithic MICs. Comparison of both MICs.420%VDistributed and lumped elements of integrated circuits - capacitors, inductors, resistors, terminations, attenuators, resonators and discontinuities.520%VIDiode control devices – switches, attenuators, limiters. Diode phase shifter. Circulators and isolators.2	III	Microwave Network Analysis – Equivalent voltages and currents, Impedance and Admittance matrices, Scattering matrix, The transmission matrix.	3	15%
IVperiodic structures and terminated periodic structures, Filter design by image parameter method – Constant k, m-derived and composite. Filter design by insertion loss method. Filter transformation and implementation.715%SECOND INTERNAL EXAMVIntroduction to MICSs:-Technology of hybrid MICs, monolithic MICs. Comparison of both MICs.420%Planar transmission lines such as stripline, microstrip line, and slotline.320%VIDistributed and lumped elements of integrated circuits - capacitors, inductors, resistors, terminations, attenuators, resonators and 		with lumped elements, Single stub tuning, Double stub tuning.	4	
VIntroduction to MICSs:-Technology of hybrid MICs, monolithic MICs. Comparison of both MICs.420%Planar transmission lines such as stripline, microstrip line, and slotline.3320%VIDistributed and lumped elements of integrated circuits - capacitors, inductors, resistors, terminations, attenuators, resonators and discontinuities.520%VIDiode control devices - switches, attenuators, limiters. Diode phase220%	IV	periodic structures and terminated periodic structures, Filter design by image parameter method – Constant k, m-derived and composite. Filter design by insertion loss method. Filter	7	15%
VMICs. Comparison of both MICs.420%Planar transmission lines such as stripline, microstrip line, and slotline.33VIDistributed and lumped elements of integrated circuits - capacitors, inductors, resistors, terminations, attenuators, resonators and discontinuities.520%VIDiode control devices – switches, attenuators, limiters. Diode phase220%	SECOND INTERNAL EXAM			
Planar transmission lines such as stripline, microstrip line, and slotline. 3 Distributed and lumped elements of integrated circuits - capacitors, inductors, resistors, terminations, attenuators, resonators and discontinuities. 5 VI Diode control devices – switches, attenuators, limiters. Diode phase 20%	N7	Introduction to MICSs:-Technology of hybrid MICs, monolithic MICs, Comparison of both MICs.		
VIinductors, resistors, terminations, attenuators, resonators and discontinuities.520%Diode control devices – switches, attenuators, limiters. Diode phase220%	v	1	3	20%
- 3	VI	inductors, resistors, terminations, attenuators, resonators and	5	20%
		-	2	

END SEMESTER EXAM

Question Paper Pattern

The question paper shall consist of three parts. Part A covers modules I and II, Part B covers modules III and IV, and Part C covers modules V and VI. Each part has three questions uniformly covering the two modules and each question can have maximum four subdivisions. In each part, any two questions are to be answered. Mark patterns are as per the syllabus with 70% for theory and 30% for logical/numerical problems, derivation and proof.

2014

COURSE				YEA	R OF			
CODE	COURSE NAME		L-T-P-C	INTROD				
	SPEECH AND AUDIO SI	IGNAL						
EC463	PROCESSING		3-0-0-3	20	16			
Prerequisite	EC301 Digital Signal Processing							
Course obje	tives:							
	miliarize the basic mechanism of			ne basic co	ncepts of			
	methods for speech analysis and parametric representation of speech.							
-	e an overall picture about various a				1 4 11			
	npart ideas of Perception of So otion and rendering.	ound, Psycho-	acoustic ana	lysis, Spati	al Audio			
	roduce Audio Compression Scheme	A 6	IL A					
	beech production, Time domain		wency domai	n analysis	Censtral			
	analysis, Speech coding, Speech i							
	Signal Processing Models of Aud							
	otion and rendering, Audio comp							
	, Transform coding of digital audio							
Expected ou								
	will be able to							
	stand basic concepts of speech		•	-	oding and			
	ametric representation of speech an			ations				
	op systems for various applications Signal processing models of sound		0	of perceptic	on models			
	audio signal processing.	i perception an	iu application	or perception	JII IIIOUEIS			
	ment audio compression algorithms	s and standards	5.					
Text Books:	r							
1. Dou	glas O'Shaughnessy, Speech Com	nmunications:	Human & M	lachine, IE	EE Press,			
	lcover 2/e, 1999; ISBN: 078033449							
	on Morgan and Ben Gold, Speec							
	eption Speech and Music, July 1999	9, John Wiley	& Sons, ISBN	I: 04713515	547			
References:	C. I.							
	d G. Childers, Speech Processing	and Synthesis	s Toolboxes,	John Wiley	v & Sons,			
	mber 1999; ISBN: 0471349593		D C H	11 1004				
	er and Juang, Fundamentals of Specer and Schafer, Digital Processing of the second secon							
	as F. Quatieri, Discrete-Time Spe				Practice			
	ce Hall; ISBN: 013242942X; 1/e		occssing. Th	incipies and	Theree,			
		se Plan						
					End			
Module	Course conte	onts		Hours	Sem.			
Wibuute	Course conta	ciits		110015	Exam			
-				-	Marks			
	peech Production: Acoustic theo							
	beech Analysis: Short-Time Speec alysis (Short time energy, short tim	-			15%			
	rametric representation of speech:		-		13 /0			
	PC Analysis (LPC model, Auto corr							
			1	1	<u> </u>			

II	Frequency domain analysis (Filter Banks, STFT, Spectrogram),Cepstral Analysis, MFCC.Fundamentals of Speech recognition and Text-to-speech conversion	8	15%
III	Speech coding, speech enhancement, Speaker Verification, Language Identification	7	15%
IV	Signal Processing Models of Audio Perception: Basic anatomy of hearing System. Auditory Filter Banks, Psycho-acoustic analysis: Critical Band Structure, Absolute Threshold of Hearing, Simultaneous Masking, Temporal Masking, Quantization Noise Shaping, MPEG psycho-acoustic model.	6	15%
	SECOND INTERNAL EXAM		
v	Audio compression methods: Sampling rate and bandwidth requirement for digital audio, Redundancy removal and perceptual irrelevancy removal, Transform coding of digital audio: MPEG2-AAC coding standard, MDCT and its properties, Pre-echo and pre-echo suppression, Loss less coding methods.	7	20%
VI	Spatial Audio Perception and rendering: The physical and psycho-acoustical basis of sound localization and space perception. Spatial audio standards. Audio quality analysis: Objective analysis methods- PEAQ, Subjective analysis methods - MOS score, MUSHRA score	6	20%
	END SEMESTER EXAM		

The question paper shall consist of three parts. Part A covers modules I and II, Part B covers modules III and IV, and Part C covers modules V and VI. Each part has three questions uniformly covering the two modules and each question can have maximum four subdivisions. In each part, any two questions are to be answered. Mark patterns are as per the syllabus with 50% for theory and 50% for logical/numerical problems, derivation and proof.

2014

COURSE			YEAR OF
CODE	COURSE NAME	L-T-P-C	INTRODUCTION
EC465	MEMS	3-0-0 -3	2016

Prerequisite : NIL

Course objectives:

- To understand the operation of major classes of MEMS devices/systems
- To give the fundamentals of standard micro fabrication techniques and processes
- To understand the unique demands, environments and applications of MEMS devices

Syllabus:

MEMS and Microsystems applications, Review of Mechanical concepts, Actuation and Sensing techniques, Scaling laws in miniaturization, Materials for MEMS, Micro System fabrication techniques, Micro manufacturing, Micro system Packaging, Bonding techniques for MEMS, Overview of MEMS areas.

Expected outcome:

The student will be able to:

- i. Understand the working principles of micro sensors and actuators
- ii. Understand the application of scaling laws in the design of micro systems
- iii. Understand the typical materials used for fabrication of micro systems
- iv. Understand the principles of standard micro fabrication techniques
- v. Appreciate the challenges in the design and fabrication of Micro systems

Text Books:

- 1. Chang Liu, Foundations of MEMS, Pearson 2012
- 2. Tai-Ran Hsu, MEMS and Microsystems Design and Manufacture, TMH, 2002

References:

- 1. Chang C Y and Sze S. M., VLSI Technology, McGraw-Hill, New York, 2000
- 2. Julian W Gardner, Microsensors: Principles and Applications, John Wiley & Sons, 1994
- 3. Mark Madou, Fundamentals of Micro fabrication, CRC Press, New York, 1997
- 4. Stephen D. Senturia, Microsystem design, Springer (India), 2006.
- 5. Thomas B. Jones, Electromechanics and MEMS, Cambridge University Press, 2001

	Course Plan		
Module	Course content (42hrs) 2014	Hours	End Sem. Exam Marks
I	MEMS and Microsystems: Applications – Multidisciplinary nature of MEMS – principles and examples of Micro sensors and micro actuators – micro accelerometer –comb drives - Micro grippers – micro motors, micro valves, micro pumps, Shape Memory Alloys.	4	
	Review of Mechanical concepts: Stress, Strain, Modulus of Elasticity, yield strength, ultimate strength – General stress strain relations – compliance matrix. Overview of commonly used mechanical structures in MEMS - Beams, Cantilevers, Plates, Diaphragms – Typical applications	3	15%

	Flexural beams: Types of Beams, longitudinal strain under pure				
	bending – Deflection of beams – Spring constant of cantilever – Intrinsic stresses	3	1507		
II	Actuation and Sensing techniques : Thermal sensors and actuators, Electrostatic sensors and actuators , Piezoelectric sensors and actuators, magnetic actuators	4	15%		
	FIRST INTERNAL EXAM				
Ш	Scaling laws in miniaturization - scaling in geometry, scaling in rigid body dynamics, Trimmer force scaling vector, scaling in electrostatic and electromagnetic forces, scaling in electricity and fluidic dynamics, scaling in heat conducting and heat convection.	5	15%		
	Materials for MEMS – Silicon – Silicon compounds – Silicon Nitride, Silicon Dioxide, Silicon carbide, Poly Silicon, GaAs, Silicon Piezo resistors,	4			
IV	Polymers in MEMS – SU-8, PMMA, PDMS, Langmuir – Blodgett Films, Micro System fabrication – Photolithography – Ion implantation- Diffusion – Oxidation – Chemicalvapour deposition – Etching	5	15%		
	SECOND INTERNAL EXAM				
V	Overview of Micro manufacturing – Bulk micro manufacturing, Surface micro machining , LIGA process –Microstereo lithography	6	20%		
	Micro system Packaging: general considerations in packaging design – Levels of Micro system packaging	3			
VI	Bonding techniques for MEMS : Surface bonding , Anodic bonding , Silicon - on - Insulator , wire bonding , Sealing – Assembly of micro systems	3	20%		
	Overview of MEMS areas : RF MEMS, BioMEMS, MOEMS, NEMS	2			
	END SEMESTER EXAM				

The question paper shall consist of three parts. Part A covers modules I and II, Part B covers modules III and IV, and Part C covers modules V and VI. Each part has three questions uniformly covering the two modules and each question can have maximum four subdivisions. In each part, any two questions are to be answered. Mark patterns are as per the syllabus with 70% for theory and 30% for logical/numerical problems, derivation and proof.

Estd.

COURS				YEAI				
CODE				INTROD				
EC469		C DEVICES	3-0-0-3	20	16			
Prerequisite: NIL								
Course ob	-							
	know the physics of absorption,	recombination ar	nd photoemissior	n from				
	niconductors.							
	analyse different types of photo			-				
	• To discuss different LED structures with material properties and reliability aspects.							
	explain optical modulators and o			1				
	illustrate different types of lasers	with distinct pro	operties.					
Syllabus:	to Long balance of	ACEDO NEGLA	1.1.4	W/L:4 . 1: .				
	ocesses in semiconductors – L							
	odulators - optical switching and onic ICs - Introduction to optical		optical memory-	Optical d	election -			
Expected		components						
	ts will be able to:							
	blain the property of absorption,	recombination an	nd photoemission	in semico	nductors			
	strate different types of lasers wi		1		nauetors.			
	blain different LED structures wi							
	alyse different types of photo det							
	plain optical modulators and opti							
Text Book								
1. Pall	b Bhattacharya: Semiconductor	O <mark>pt</mark> oelectronic D	evices, Pearson	, 20 <mark>0</mark> 9				
2. Yai	iv, Photonics Optical Electron	ics in modern	communication,	6/e ,Oxf	ord Univ			
Pre	ss,2006.							
Reference	5:							
1. Ala	stair Buckley, Organic Light-Em	itting Diodes, W	oodhead, 2013.					
2. B E	Saleh and M C Teich, Fundame	ntals of Photonic	s:, Wiley-Intersc	<mark>zie</mark> nce, 199	1			
3. Bai	dyopadhay, Optical communicat	toion and network	ks, PHI, 2014.					
	nbaev, Scheiner, Fiberoptic Com		U .	, 2001.				
5. Pip	rek, Semiconductor Optoelectron	ic Devices, Elsev	vier, 2008.					
6. Xu	h Li, Optoelectronic Devices Des	ign Modelling ar	nd Simulation, C	ambridge				
Un	versity Press, 2009							
	С	ourse Plan						
		014	1		End			
Module	Course con	tent (42hrs)		Hours	Sem.			
Mouule	Course con	tent (42115)		Hours	Exam			
					Marks			
	1 1	conductors –	electron hole					
Ι	recombination, absorption, Fra			7	15%			
-	quantum confined Stark effect	-	-	,	10 /0			
	recombination heat generation a							
	Lasers - threshold condition	-	-					
II	mechanisms, axial and transve		-	7	15%			
	lasers, distributed feedback las		-	,	/0			
	lasers, tunneling based lasers, m	odulation of lase	rs.					

	FIRST INTERNAL EXAM		
III	Nitride light emitters, nitride material properties, InGaN/GaN LED, structure and working, performance parameters, InGaN/GaN Laser Diode, structure and working, performance parameters. White-light LEDs, generation of white light with LEDs, generation of white light by dichromatic sources, ,generation of white light by trichromatic sources, temperature dependence of trichromatic, 7generation of white light by tetrachromatic and pentachromatic sources, white-light sources based on wavelength converters.	9	15%
IV	Optical modulators using pn junction, electro-optical modulators, acousto-optical modulators, Raman-Nath modulators, Franz- Keldysh and Stark effect modulators, quantum well electro- absorption modulators, optical switching and logic devices, optical memory.	5	15%
	SECOND INTERNAL EXAM		
V	Optical detection – PIN, APD, modulated barrier photodiode, Schottky barrier photodiode, wavelength selective detection, micro cavity photodiodes. Optoelectronic ICs, advantages, integrated transmitters and receivers, guided wave devices. Working of LDR, liquid crystal display, structure, TFT display, structure, polymer LED, organic LED.	7	20%
VI	Introduction to optical components, directional couplers, multiplexers, attenuators, isolators, circulators, tunable filters, fixed filters, add drop multiplexers, optical cross connects, wavelength convertors, optical bistable devices.	7	20%
	END SEMESTER EXAM		

The question paper shall consist of three parts. Part A covers modules I and II, Part B covers modules III and IV, and Part C covers modules V and VI. Each part has three questions uniformly covering the two modules and each question can have maximum four subdivisions. In each part, any two questions are to be answered. Mark patterns are as per the syllabus with 50% for theory and 50% for logical/numerical problems, derivation and proof.

Estd.